

KSA916

PNP EPITAXIAL SILICON TRANSISTOR

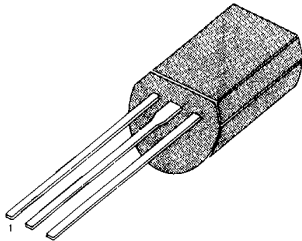
AUDIO POWER AMPLIFIER

- Driver Stage Amplifier
- Complement to KSC2316

ABSOLUTE MAXIMUM RATINGS (T_A=25 °C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	-120	V
Collector-Emitter Voltage	V _{CEO}	-120	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-800	mA
Collector Dissipation	P _C	900	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

TO-92L



1. Emitter 2. Collector 3. Base

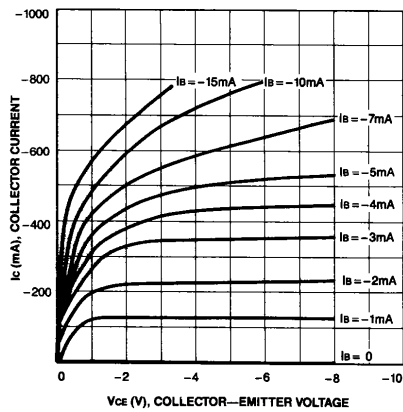
ELECTRICAL CHARACTERISTICS (T_A=25 °C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = -1mA I _E =0	-120			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = -10mA, I _B =0	-120			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -1mA, I _C =0	-5			V
Collector Cut-off Current	I _{CBO}	V _{CB} = -120V, I _E =0			-0.1	μA
DC Current Gain	h _{FE1}	V _{CE} = -5V, I _C = -10mA	60			
	h _{FE2}	V _{CE} = -5V, I _C = -100mA	80		240	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C = -500mA, I _B = -50mA			-1	V
Current-Gain-Bandwidth Product	f _T	V _{CE} = -5V, I _C = -100mA		120		MHz
Output Capacitance	C _{OB}	V _{CB} = -10V, I _E =0, f=1MHz			40	pF

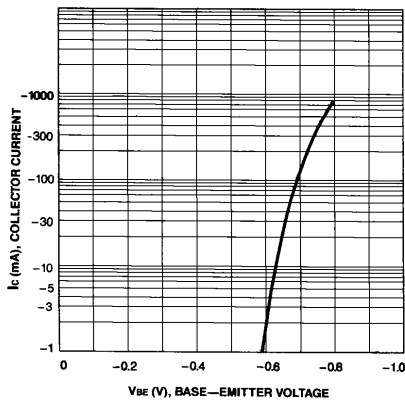
h_{FE} CLASSIFICATION

Classification	O	Y
h _{FE}	80-160	120-240

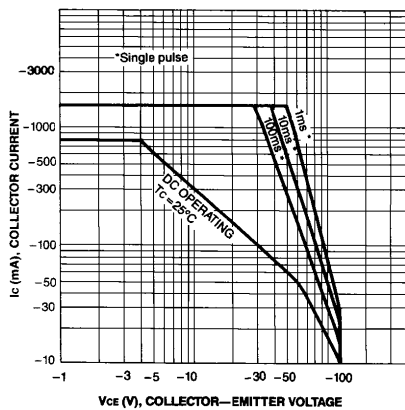
STATIC CHARACTERISTIC



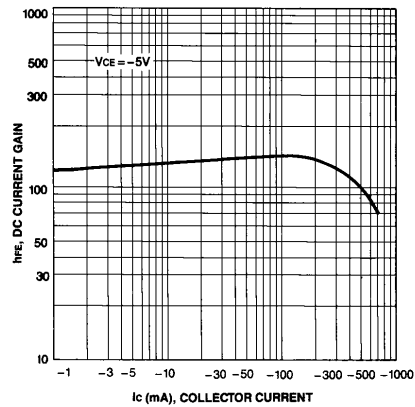
BASE-EMITTER ON VOLTAGE



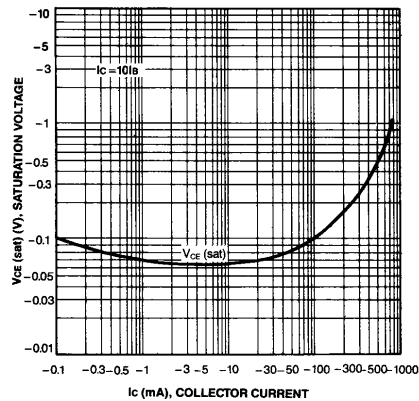
SAFE OPERATING AREA



DC CURRENT GAIN



COLLECTOR-EMITTER SATURATION VOLTAGE



POWER DERATING

